

VHF/ UHF-Tuner-IC

Description

This tuner IC requires a power supply of 12 V and performs the function of three separate oscillators and

mixers, SAWF-driver, L.O.-output and tri-state band switch. Applications are 12 V TV- and VCR-tuners.

Features

- Frequency range from 48 to 860 MHz
- Band A: balanced high impedance mixer input and amplitude controlled oscillator
- Band B + C: balanced low impedance mixer input and symmetrical oscillator
- Balanced L.O.-output for prescalers or PLL
- SAW filter driver with low impedance output

- Voltage regulator for stable operating characteristics
- ESD protection on all pins except oscillator pins and RF-inputs

Benefits

- The integration of 3 bands allows to design economical 3-band tuners

Block Diagram

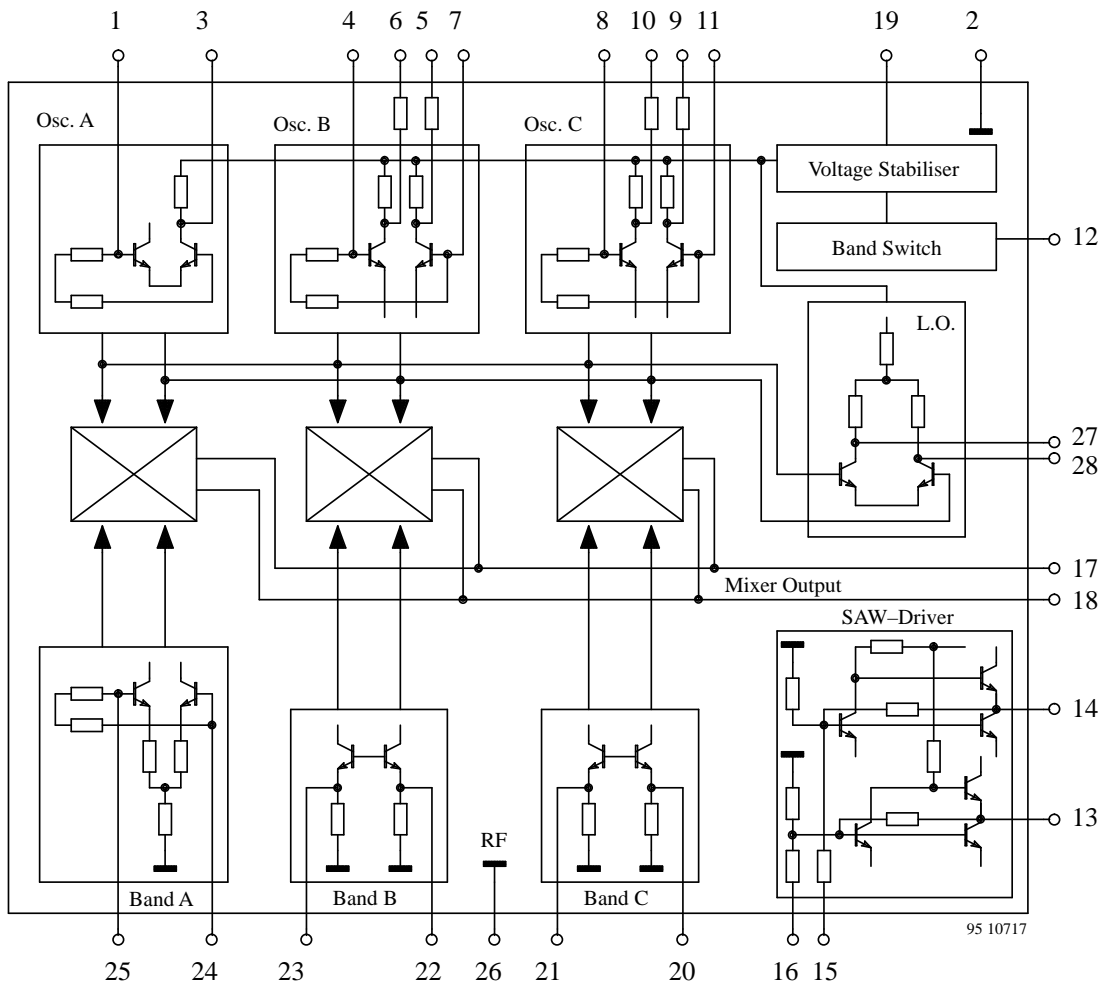
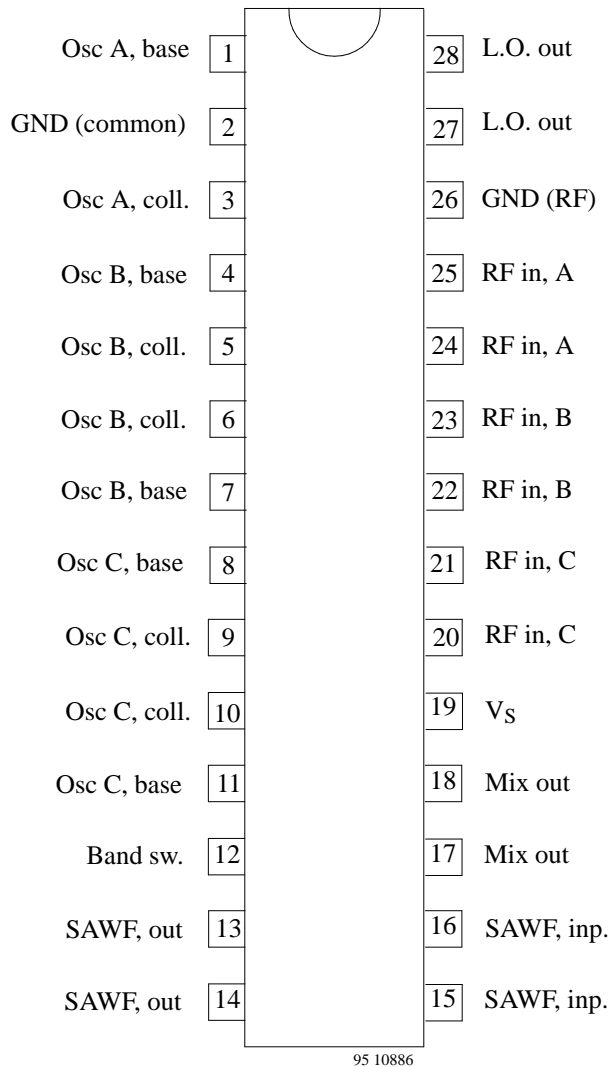


Figure 1. Block diagram

Pin Description



Pin	Symbol	Function
1	Osc A, base	Oscillator band A, base
2	GND (common)	Ground, common
3	Osc A, coll.	Oscillator band A, collector
4, 7	Osc B, base	Oscillator band B, bases
5, 6	Osc B, coll.	Oscillator band B, collectors
8, 11	Osc C, base	Oscillator band C, bases
9, 10	Osc C, coll.	Oscillator band C, collectors
12	Band sw.	Tri-state band switch
13, 14	SAWF, out	SAW filter driver outputs
15, 16	SAWF, inp.	SAW filter driver inputs
17, 18	Mix out	Mixer outputs, open collector
19	V _S	Supply voltage V _S
20, 21	RF in, C	RF inputs, band C
22, 23	RF in, B	RF inputs, band B
24, 25	RF in, A	RF inputs, band A
26	GND (RF)	Ground, RF part
27, 28	L.O. out	L.O.-outputs

Ordering Information

Extended Type Number	Package	Remarks
U2300B-FLG3	SO28	Taped and reeled

Absolute Maximum Ratings

All voltages are referred to GND, Pin 2

Parameters	Symbol	Min.	Typ.	Max.	Unit
Supply voltage	Pin 19 V _S			13.5	V
RF inputs	Pin 20-25			5.0	V
IF outputs	Pin 17-18			13.5	V
Tri-state switch voltage	Pin 12 ViDSW			13.5	V
Junction temperature	T _{jmax}			125	°C
Storage temperature	T _{stg}	-40		125	°C

Operating Range

All voltages are referred to GND, Pin 2

Parameters	Test Conditions / Pins	Symbol	Min.	Typ.	Max.	Unit
Supply voltage	Pin 17-19	V_s	10.8	12	13.2	V
Ambient temperature		T_{amb}	-25		75	°C
Thermal resistance	Test conditions page 5, Package SO-28	R_{thJA}		70		K/W

Electrical Characteristics

Test conditions: $V_s = 12$ V, $T_{amb} = 25^\circ\text{C}$, unless otherwise specified, reference point Pin 2, referred to test circuit page 5

Parameters	Test Conditions / Pins	Symbol	Min.	Typ.	Max.	Unit
Supply voltage	Pin 17-19	V_s	10.8	12.0	13.2	V
Supply current	Pin 17-19	I_s		42	50	mA
Band switch						
Voltage Band A	Pin 12	VSWA	0	0	1.0	V
Voltage Band B	Pin 12	VSWB	1.6	2.0	2.4	V
Voltage Band C	Pin 12	VSWC	3.4	4.0	5.0	V
Switching current	VSW = 5 V Pin 12	ISW			100	μA
L.O.-output						
L.O. level each output	$R_L = 50$ Ohm Pin 27, 28	PLO	-25		-17	dBm
SAW filter driver $f_i = 36$ MHz						
Input impedance	Pin 15, 16	Z_{iSAW}		450		Ohm
Output impedance	Pin 13, 14	Z_{oSAW}		70		Ohm
Voltage gain	15, 16 \rightarrow 13, 14	G_{vSAW}		18		dB
Band A						
Input frequency range	Pin 24	f_{iA}	48		170	MHz
Input impedance	Figure 3 Pin 24	S_{11A}				
Gain (note 4)	Pin I/P to O/P	GA		29		dB
Noise figure DSB (note 2)	Pin I/P to O/P					
	$f_{iA} = 50$ MHz	NF		11.5		dB
	$f_{iA} = 150$ MHz	NF		12		dB
Input level for (note 3):	Each carrier					
IM3 (interm. of 3rd order)	$f_{iA} = 71$ MHz Pin I/P	V_{iA}		-21		dBm
IM2 (interm. of 2nd order)	$f_{iA} = 71$ MHz Pin I/P	V_{iA}		-21		dBm
Band B (note 1)						
Input frequency range	Pin 22, 23	f_{iB}	170		470	MHz
Input impedance	Figure 3 Pin 22, 23	S_{11B}				
Gain (note 4)	Pin I/P to O/P	GB		33		dB
Noise figure DSB (note 2)	Pin I/P to O/P					
	$f_{iB} = 200$ MHz	NF		9.5		dB
	$f_{iB} = 450$ MHz	NF		10		dB
Input level for (note 3)	Each carrier					
IM3 (interm. of 3rd order)	$f_{iB} = 300$ MHz Pin I/P	V_{iB}		-26		dBm

Parameters	Test Conditions / Pins	Symbol	Min.	Typ.	Max.	Unit
Band C (note 1)						
Input frequency range	Pin 20, 21	fiC	470		860	MHz
Input impedance	Figure 3 Pin 20, 21	S11C				
Gain	Pin I/P to O/P	GC		33		dB
Noise figure DSB (note 2)	Pin I/P to O/P fiC = 500 MHz	NF		10.5		dB
		NF		11.5		dB
Input level for (note 3):	Each carrier					
IM3 (interm. of 3rd order)	fiC = 600 MHz Pin I/P	ViC		-26		dBm

Notes

- 1 The RF input B and C are symmetrical driven by means of a hybrid for 180° phase shifting, consequently the source impedance is 100 Ω. All other impedance for RF tests is 50 Ω.
- 2 The noise figure (NF) is the value for double-side-band measurement.
- 3 The intermodulation test (2-carrier-method) which is made on IF-centre is in reference to a signal-to-IM ratio of 60 dB.
- 4 Gain is the ratio of the voltage at the primary coil of L5 to the available voltage at the input.

Test and Principle Application Circuit

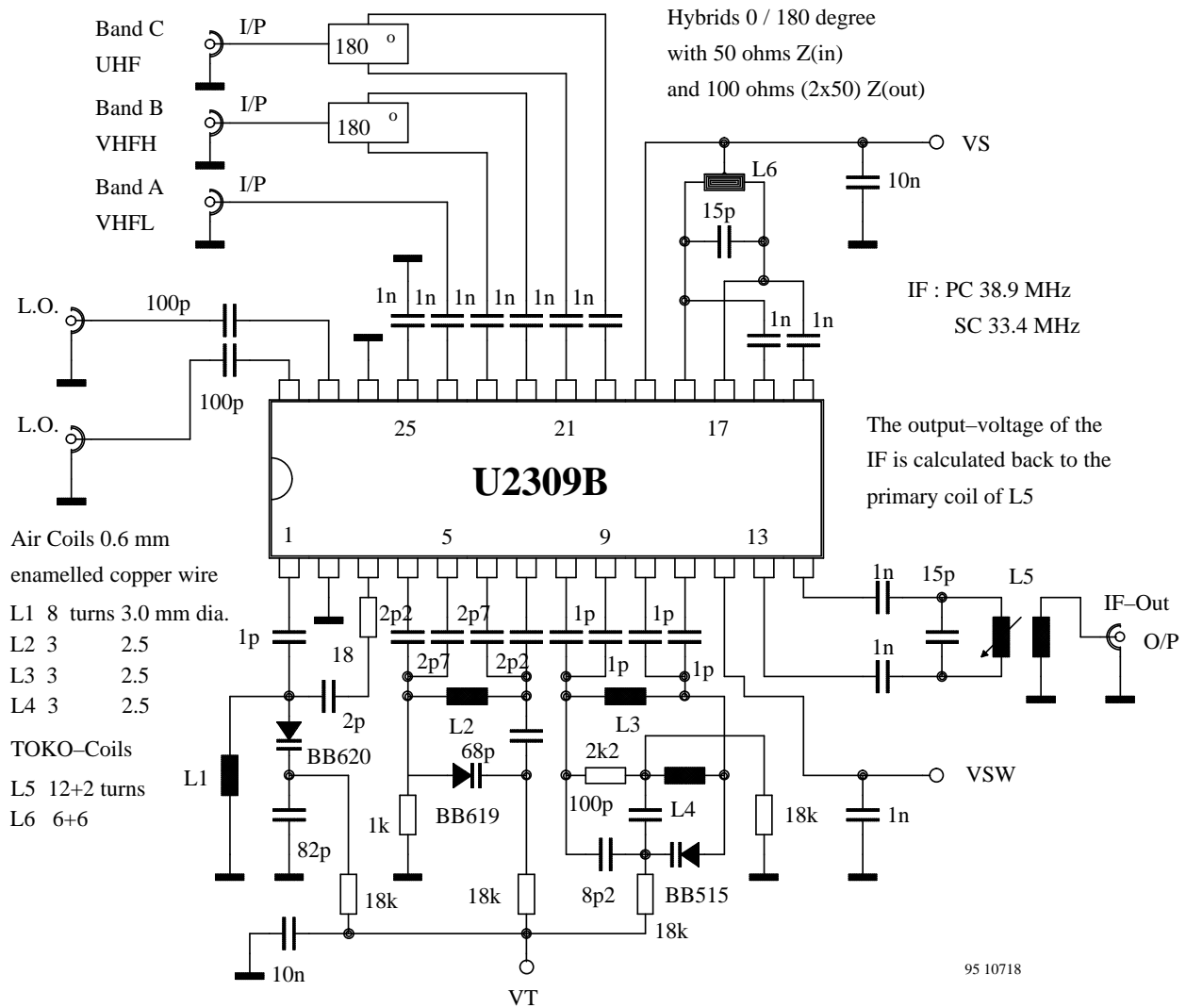


Figure 1. Test and principle application circuit

PCB for the R_{thJA} -Measurement

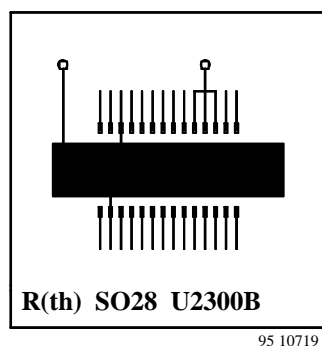
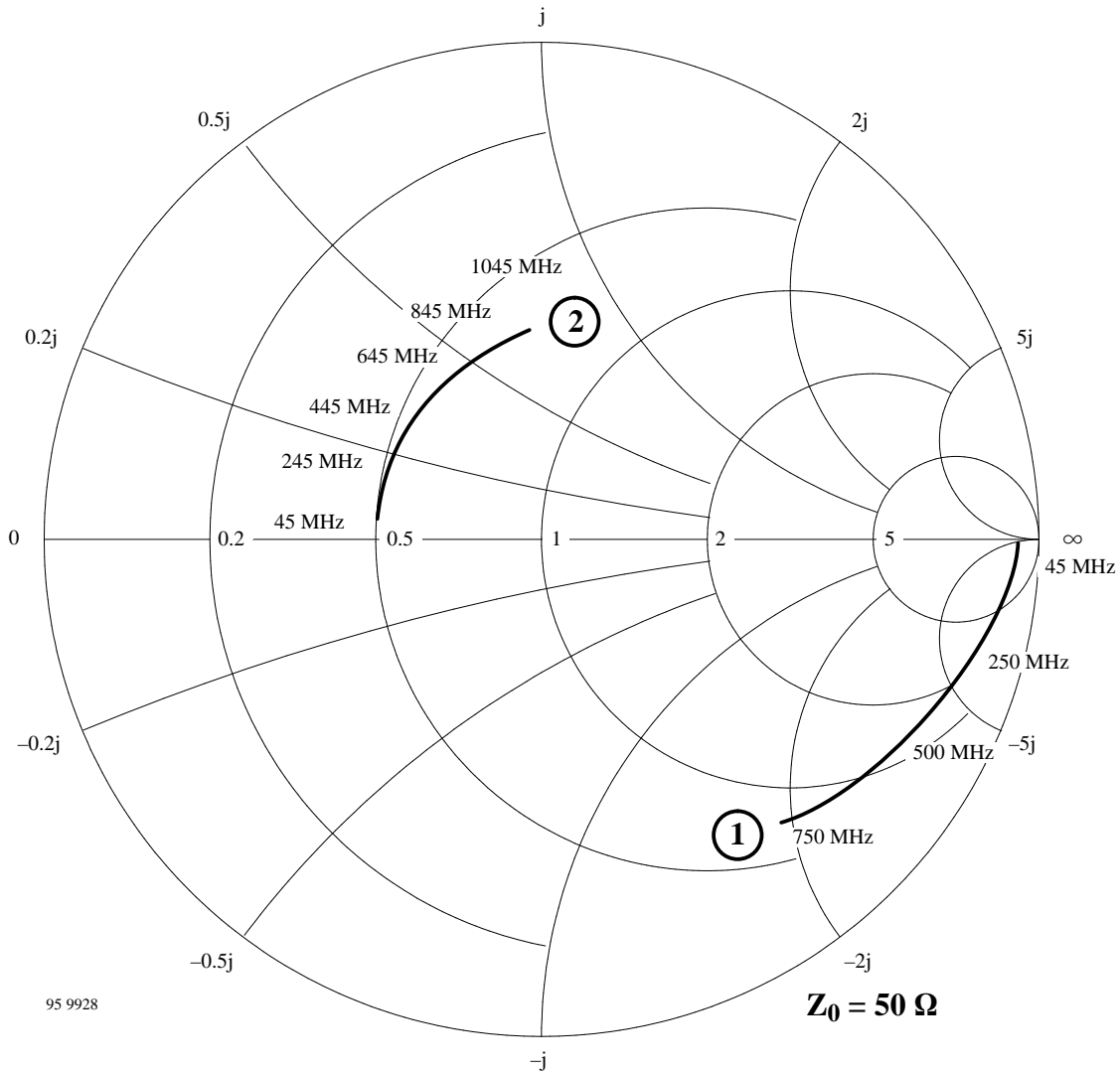


Figure 2. PCB for the R_{thJA} -Measurement

Input Impedance Mixer Band A (S11A), B and C (S11B/C)

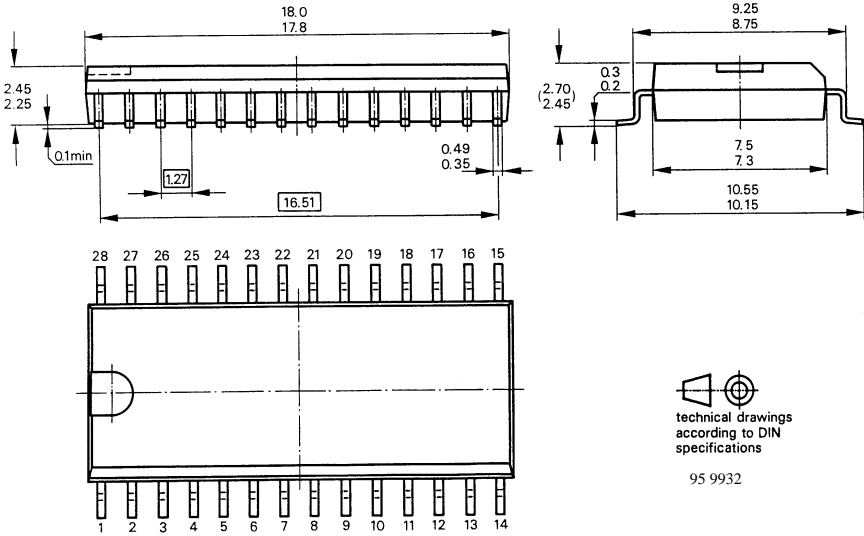


- 1 **VHF-Low**
Normalised to 50Ω , measuring range 45 MHz to 750 MHz.
- 2 **UHF-High and UHF**
Normalised to 50Ω , measuring range 45 MHz to 1045 MHz. Both inputs are driven symmetrical.
The output impedance of hybrid is 100Ω , the measured levels are then calculated in reference to 50Ω .

Figure 3. Input impedance mixer band A (S11A), B and C (S11B/C)

Dimensions in mm

Package: SO28



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2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

TEMIC TELEFUNKEN microelectronic GmbH semiconductor division has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

TEMIC can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

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